

Data Sheet April 1999 File Number 2907.4

2.5MHz, Precision Operational Amplifier

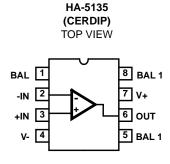
The Intersil HA-5135 is a precision operational amplifier manufactured using a combination of key technological advancements to provide outstanding input characteristics.

A Super Beta input stage is combined with laser trimming, dielectric isolation and matching techniques to produce $75\mu V$ (Maximum) input offset voltage and $0.4\mu V/^{O}C$ input offset voltage average drift. Other features enhanced by this process include $9nV/\sqrt{Hz}$ (Typ) Input Noise Voltage, 1nA Input Bias Current and 140dB Open Loop Gain.

These features coupled with 120dB CMRR and PSRR make the HA-5135 an ideal device for precision DC instrumentation amplifiers. Excellent input characteristics in conjunction with 2.5MHz bandwidth and 0.8V/ μ s slew rate, make this amplifier extremely useful for precision integrator and biomedical amplifier designs. This amplifier is also well suited for precision data acquisition and for accurate threshold detector applications.

HA-5135 offers added features over the industry standard OP-07 in regards to bandwidth and slew rate specifications. For the military grade product, refer to the HA-5135/883 data sheet.

Pinout



NOTE: Both BAL 1 pins are connected together internally.

Features

| • Low Offset Voltage |
|--|
| • Low Offset Voltage Drift 0.4 μ V/ 0 C |
| • Low Noise |
| Open Loop Gain |
| • Unity Gain Bandwidth |
| All Bipolar Construction |

Applications

- · High Gain Instrumentation
- · Precision Data Acquisition
- · Precision Integrators
- · Biomedical Amplifiers
- · Precision Threshold Detectors

Ordering Information

| PART NUMBER | TEMP. RANGE (°C) | | |
|-------------|---------------------|-------------|-------|
| HA7-5135-5 | 0 to 75 | 8 Ld CERDIP | F8.3A |

Absolute Maximum Ratings

Thermal Information

| Thermal Resistance (Typical, Note 2) | θ_{JA} (oC/W) | θ_{JC} (oC/W) |
|---|----------------------|--|
| CERDIP Package | 135 | 50 |
| Maximum Junction Temperature (Note 1) . | | |
| Maximum Storage Temperature Range | 6 | 5 ^o C to 150 ^o C |
| Maximum Lead Temperature (Soldering 1 | 0s) | 300°C |
| | | |

Operating Conditions

| Temperature Ranges | |
|--------------------|-------------|
| HA-5135-5 | 0°C to 75°C |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

- 1. Maximum power dissipation, including output load, must be designed to maintain the maximum junction temperature below 175°C.
- 2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications $V_{SUPPLY} = \pm 15V$

| PARAMETER | | TEMP. | HA-5135-5 | | | |
|-------------------------------|--|----------|-----------|------|------|--------------------|
| | TEST CONDITIONS | (°C) | MIN | TYP | MAX | UNITS |
| INPUT CHARACTERISTICS | | ' | | ' | | • |
| Offset Voltage | | 25 | - | 10 | 75 | μV |
| | | Full | - | 50 | 130 | μV |
| Average Offset Voltage Drift | | Full | - | 0.4 | 1.3 | μV/ ^o C |
| Bias Current | | 25 | - | ±1 | ±4 | nA |
| | | Full | - | - | ±6 | nA |
| Bias Current Average Drift | | Full | - | 0.02 | 0.04 | nA/ ^o C |
| Offset Current | | 25 | - | - | 4 | nA |
| | | Full | - | - | 5.5 | nA |
| Offset Current Average Drift | | Full | - | 0.02 | 0.04 | nA/ ^o C |
| Common Mode Range | | Full | ±12 | - | - | V |
| Differential Input Resistance | | 25 | 20 | 30 | - | ΜΩ |
| Input Noise Voltage (Note 3) | 0.1Hz to 10Hz | 25 | - | - | 0.6 | μV _{P-P} |
| Input Noise Voltage Density | f = 10Hz | 25 | - | 13.0 | 18.0 | nV/√Hz |
| (Note 3) | f = 100Hz | | - | 10.0 | 13.0 | nV/√Hz |
| | f = 1000Hz | | - | 9.0 | 11.0 | nV/√Hz |
| Input Noise Current (Note 3) | 0.1Hz to 10Hz | 25 | - | 15 | 30 | pA _{P-P} |
| Input Noise Current Density | f = 10Hz | 25 | - | 0.4 | 0.8 | pA/√Hz |
| (Note 3) | f = 100Hz | | - | 0.17 | 0.23 | pA/√Hz |
| | f = 1000Hz | | - | 0.14 | 0.17 | pA/√Hz |
| TRANSFER CHARACTERISTICS | | ' | | | | |
| Large Signal Voltage Gain | $V_{OUT} = \pm 10V$, $R_L = 2k\Omega$ | 25 | 120 | 140 | - | dB |
| | | Full | 120 | - | - | dB |
| Common Mode Rejection Ratio | V _{CM} = ±10V | Full | 106 | 120 | - | dB |
| Closed Loop Bandwidth | A _{VCL} = +1 | 25 | 0.6 | 2.5 | - | MHz |
| OUTPUT CHARACTERISTICS | | ' | • | | | • |
| Output Voltage Swing | $R_L = 600\Omega$ | 25 | ±10 | ±12 | - | V |
| | | Full | ±10 | - | - | V |

Electrical Specifications $V_{SUPPLY} = \pm 15V$ (Continued)

| | | TEMP. | HA-5135-5 | | | | |
|-------------------------------|-----------------------------|-------|-----------|-----|-----|-------|--|
| PARAMETER | TEST CONDITIONS | (°C) | MIN | TYP | MAX | UNITS | |
| Full Power Bandwidth (Note 4) | $R_L = 2k\Omega$ | 25 | 8 | 10 | - | kHz | |
| Output Current | V _{OUT} = 10V | 25 | ±15 | ±20 | - | mA | |
| Output Resistance | Note 5 | 25 | - | 45 | - | Ω | |
| TRANSIENT RESPONSE (Note 6) | | | | | | | |
| Rise Time | | 25 | - | 340 | - | ns | |
| Slew Rate | | 25 | 0.5 | 0.8 | - | V/µs | |
| Settling Time (Note 7) | | 25 | - | 11 | - | μs | |
| POWER SUPPLY CHARACTERISTICS | | | | | | | |
| Supply Current | | Full | - | 1.0 | 1.7 | mA | |
| Power Supply Rejection Ratio | $V_S = \pm 5V$ to $\pm 20V$ | Full | 94 | 130 | - | dB | |

NOTES:

- 3. Not tested. 90% of units meet or exceed these specifications.
- 4. Full power bandwidth guaranteed based on slew rate measurement using: FPBW = $\frac{\text{Slew Rate}}{2\pi \text{ V}_{\text{PEAK}}}$.
- 5. Output resistance measured under open loop conditions (f = 100Hz).
- 6. Refer to test circuits section of the data sheet.
- 7. Settling time is measured to 0.1% of final value for a 10V output step and A_V = -1.

Test Circuits and Waveforms

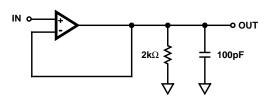
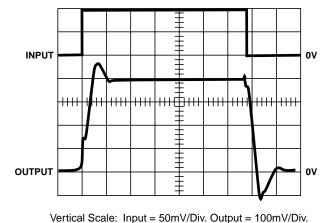
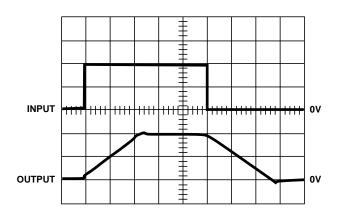


FIGURE 1. SLEW RATE AND TRANSIENT RESPONSE TEST CIRCUIT



Horizontal Scale: 1µs/Div.



Vertical Scale: 5V/Div. Horizontal Scale: 5µs/Div.

SMALL SIGNAL RESPONSE

LARGE SIGNAL RESPONSE

Test Circuits and Waveforms (Continued)

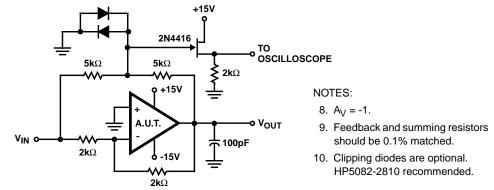
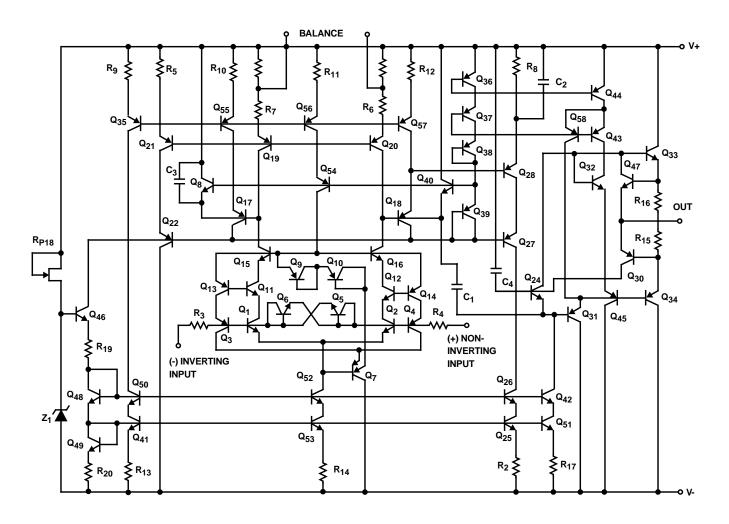


FIGURE 2. SETTLING TIME CIRCUIT

Schematic Diagram



Application Information

Power Supply Decoupling

Although not absolutely necessary, it is recommended that all power supply lines be decoupled with $0.01\mu F$ ceramic capacitors to ground. Decoupling capacitors should be located as near to the amplifier terminals as possible.

Considerations For Prototyping:

The following list of recommendations are suggested for prototyping.

- Resolving low level signals requires minimizing leakage currents caused by external circuitry. Use of quality insulating materials, thorough cleaning of insulating surfaces and implementation of moisture barriers when required is suggested.
- Error voltages generated by thermocouples formed between dissimilar metals in the presence of temperature gradients should be minimized. Isolation of low level circuity from heat generating components is recommended.
- 3. Shielded cable input leads, guard rings and shield drivers are recommended for the most critical applications.

Large Capacitive Loads

When driving large capacitive loads (>500pF), a small value resistor (\approx 50 Ω) should be connected in series with the output and inside the feedback loop.

Offset Voltage Adjustment (See Figure 3)

A $20k\Omega$ balance potentiometer is recommended if offset nulling is required. However, other potentiometer values such as $10k\Omega$, $50k\Omega$ and $100k\Omega$ may be used. The minimum adjustment range for given values is ± 2 mV. V_{OS} TC of the amplifier is optimized at minimal V_{OS} . Tested Offset Adjustment is $|V_{OS}+1$ mV| minimum referred to output.

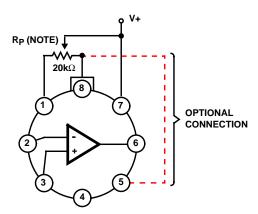


FIGURE 3. OFFSET NULLING CONNECTIONS

Saturation Recovery

Input and output saturation recovery time is negligible in most applications. However, care should be exercised to avoid exceeding the absolute maximum ratings of the device.

Differential Input Voltages

Inputs are shunted with back-to-back diodes for overvoltage protection. In applications where differential input voltages in excess of 1V are applied between the inputs, the use of limiting resistors at the inputs is recommended.

Typical Applications

The excellent input and gain characteristics of HA-5135 are well suited for precision integrator applications. Accurate integration over seven decades of frequency using HA-5135, virtually nullifies the need for more expensive chopper-type amplifiers.

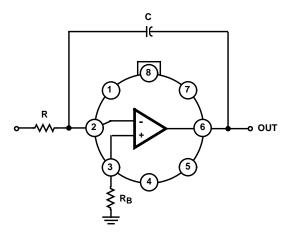
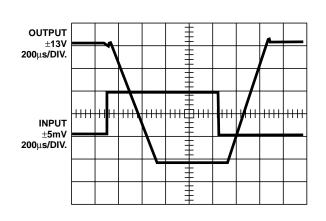


FIGURE 4. PRECISION INTEGRATOR

Low V_{OS} coupled with high open loop Gain, high CMRR and high PSRR make HA-5135 ideally suited for precision detector applications, such as the zero crossing detector shown in Figure 5.



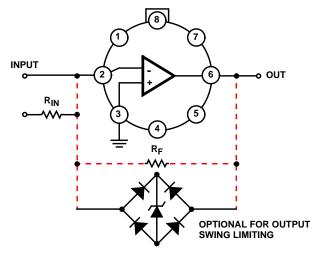


FIGURE 5. ZERO CROSSING DETECTOR

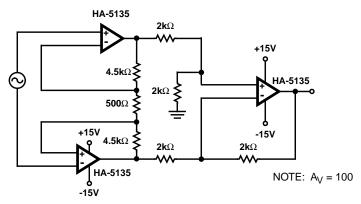


FIGURE 6. PRECISION INSTRUMENTATION AMPLIFIER

Typical Performance Curves

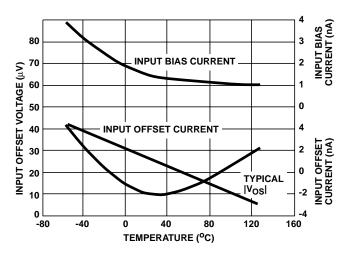


FIGURE 7. INPUT OFFSET VOLTAGE, INPUT BIAS AND OFFSET CURRENT vs TEMPERATURE

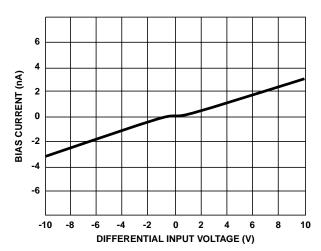


FIGURE 8. INPUT BIAS CURRENT vs DIFFERENTIAL INPUT VOLTAGE

Typical Performance Curves (Continued)

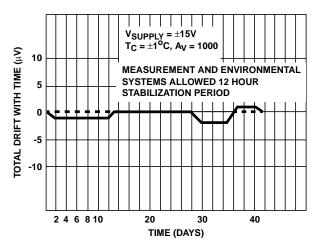


FIGURE 9. HA-5135 OFFSET VOLTAGE STABILITY vs TIME

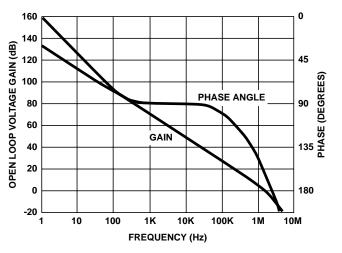


FIGURE 11. OPEN LOOP FREQUENCY RESPONSE

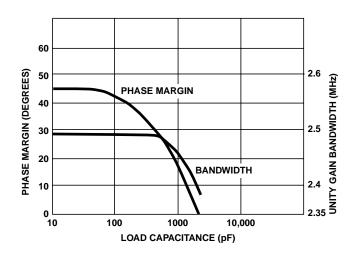


FIGURE 13. SMALL SIGNAL BANDWIDTH AND PHASE MARGIN vs LOAD CAPACITANCE

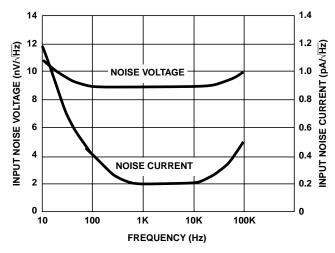


FIGURE 10. INPUT NOISE vs FREQUENCY

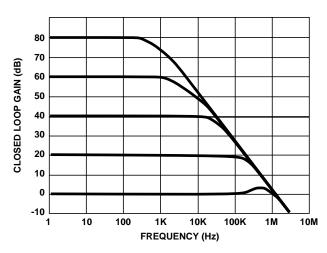


FIGURE 12. CLOSED LOOP FREQUENCY RESPONSE

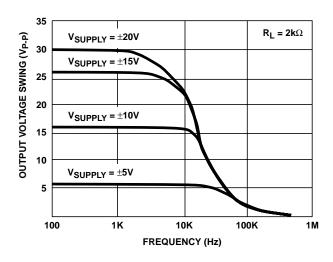


FIGURE 14. OUTPUT VOLTAGE SWING vs FREQUENCY

Typical Performance Curves (Continued)

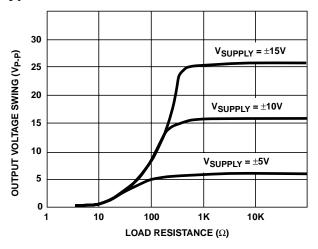


FIGURE 15. MAXIMUM OUTPUT VOLTAGE SWING vs LOAD RESISTANCE

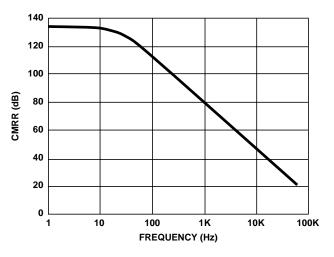


FIGURE 17. CMRR vs FREQUENCY

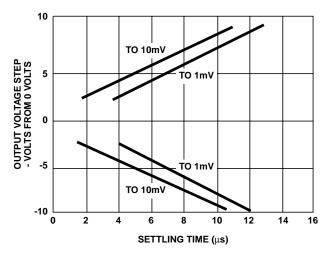


FIGURE 19. SETTLING TIME FOR VARIOUS OUTPUT STEP VOLTAGES

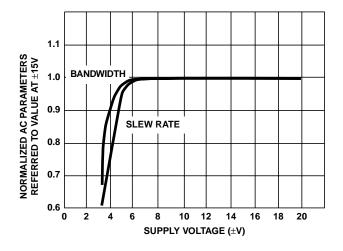


FIGURE 16. NORMALIZED AC PARAMETERS vs SUPPLY VOLTAGE

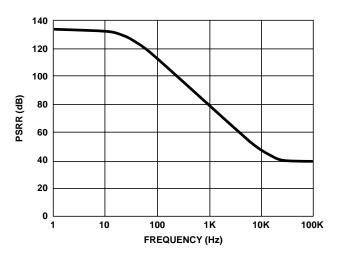


FIGURE 18. PSRR vs FREQUENCY

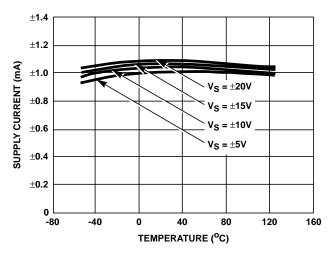


FIGURE 20. POWER SUPPLY CURRENT vs TEMPERATURE

Die Characteristics

DIE DIMENSIONS:

72 mils x 103 mils x 19 mils (1840μm x 2620μm x 483μm)

METALLIZATION:

Type: Al, 1% Cu Thickness: 16kÅ ±2kÅ

SUBSTRATE POTENTIAL (POWERED UP):

V-

Metallization Mask Layout

PASSIVATION:

Type: Nitride (Si₃N₄) over Silox (SiO₂, 5% Phos.)

Silox Thickness: 12kÅ ±2kÅ Nitride Thickness: 3.5kÅ ±1.5kÅ

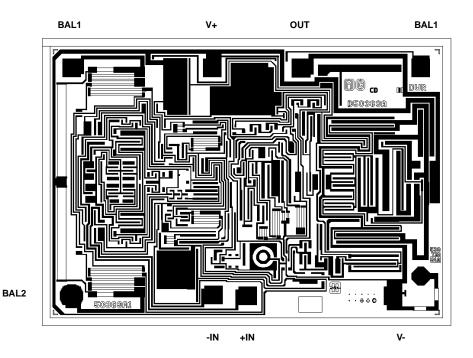
TRANSISTOR COUNT:

71

PROCESS:

Bipolar Dielectric Isolation

HA-5135



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